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Docket No. 740756-2285

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430-102  
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TC 2300 MAIL ROOM

In re Patent Application of:

Ritsuko KAWASAKI et al.

Serial No. 09/651,889

Filed: August 30, 2000

For: SEMICONDUCTOR DEVICE,  
MANUFACTURING METHOD  
THEREOF

) Group Art Unit: 2814

) Examiner: D. Farahani

) CERTIFICATE OF MAILING  
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on March 7, 2002.

) *Gwyn J. Cantrell*  
Gwyn J. Cantrell

)

### AMENDMENT

Honorable Commissioner of Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Examiner's non-final Office Action mailed December 7, 2001, please consider the following amendments and remarks in connection with the above-identified application.

### IN THE CLAIMS:

Please amend claims 1-3 and 10 as follows. Claims 1-3 and 10 are presented below in their amended form. The amendments to the above-noted claims are outlined in an Attachment to the Amendment using the conventional indication method of bracketing and underlining.

1. (Amended) A semiconductor device comprising a TFT containing an active layer having a convex portion or a concave portion in a channel forming region.

2. (Amended) A semiconductor device comprising a TFT containing an active layer having a convex portion or a concave portion in a channel forming region, wherein zero or one grain boundary is contained in the channel forming region.